TOSHIBA TLP591B

TOSHIBA PHOTOCOUPLER GaA&As IRED & PHOTO-DIODE ARRAY

TLP591B

TELECOMMUNICATION PROGRAMMABLE CONTROLLERS MOS GATE DRIVER MOS FET GATE DRIVER

The TOSHIBA TLP591B consists of an aluminum galium arsenide infrared emitting diode optically coupled to a series connected photodiode array in a six lead plastic DIP package.

TLP591B is suitable for MOS FET Gate Driver.

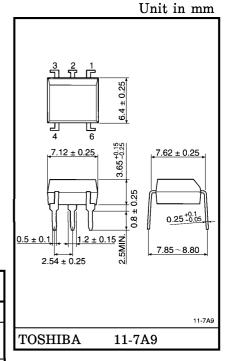
TLP591B has an internal shunt resistor to optimize switching speed.

: UL1577, File No. E67349 UL Recognized

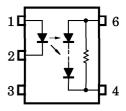
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
	Forward Current	${ m I_F}$	50	mA	
	Forward Current Derating (Ta≥25°C)	⊿I _F /°C	-0.5	mA/°C	
LEI	Pulse Forward Current (100µs pulse, 100pps)	I_{FP}	1	A	
	Reverse Voltage	$v_{ m R}$	3	V	
	Junction Temperature	T_{j}	125	°C	
ror	Forward Current	$I_{ m FD}$	50	μ A	
DETECTOR	Reverse Voltage	$v_{ m RD}$	10	V	
DE	Junction Temperature	$\mathbf{T_{j}}$	125	°C	
Sto	orage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C	
Op	erating Temperature Range	$T_{ m opr}$	-40~85	°C	
	ad Soldering Temperature Osec.)	T _{sol}	260	$^{\circ}\mathrm{C}$	
	lation Voltage C, 1 min., R.H.≦60%) (Note 1)	$BV_{\mathbf{S}}$	2500	Vrms	

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together, and pins 4 and 6 shorted together.



PIN CONFIGURATION (TOP VIEW)



: ANODE 2. : CATHODE 3.: NC

4. : CATHODE

6.: ANODE

2001-06-01

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward Current	$I_{\mathbf{F}}$	_	20	25	mA
Operating Temperature	$T_{ m opr}$	-25	_	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage	$ m V_{ m F}$	$I_{\mathbf{F}} = 10 \text{mA}$	1.2	1.4	1.7	V
ED,	Reverse Current	${ m I}_{ m R}$	$V_R=3V$		_	10	μ A
1	Capacitance	C_{T}	V=0, f=1MHz		30	60	pF
OR	Forward Voltage	$ m v_{FD}$	$I_{\text{FD}} = 10 \mu \text{A}$		7	_	V
Ğ	Reverse Current	${ m I_{RD}}$	$V_{RD} = 10V$		7	_	μ A
DETECT	Capacitance (Anode to Cathode)	$\mathrm{C_{TD}}$	V=0, f=1MHz	_	_	_	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Open Voltage	v_{oc}	$I_{ m F}\!=\!20{ m mA}$	7	8	_	V
Short Current	I_{SC}	$I_{ m F}\!=\!20{ m mA}$	24	40	_	μ A

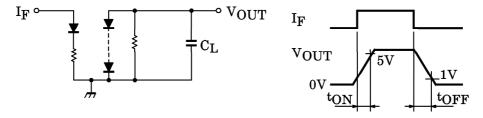
ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	$C_{\mathbf{S}}$	$V_S=0$, $f=1MHz$		0.8	_	pF
Isolation Resistance	$R_{\mathbf{S}}$	$V_S = 500V$	5×10^{10}	10^{14}	_	
Isolation Voltage	$BV_{\mathbf{S}}$	AC, 1 minute	2500	_	_	**
		AC, 1 second, in oil		5000	_	Vrms
		DC, 1 minute, in oil	_	5000	_	Vdc

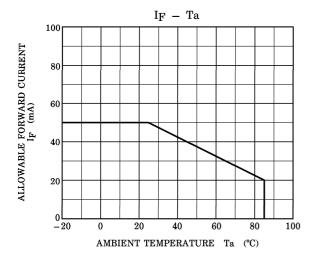
SWITCHING CHARACTERISTICS (Ta = 25°C)

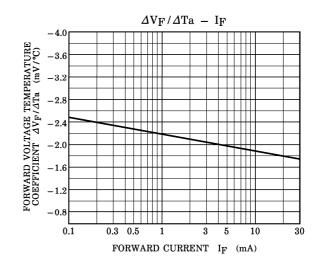
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Turn-on Time	t_{on}	$I_F = 20 \text{mA}, C_L = 1000 \text{pF}$		0.2	_	ms
Turn-off Time	$t_{ m off}$	(Fig.1)	_	3	_	ms

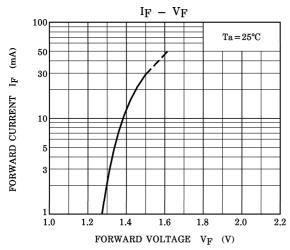
Fig.1 SWITCHING TIME TEST CIRCUIT

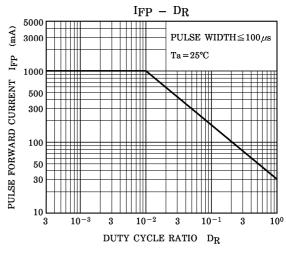


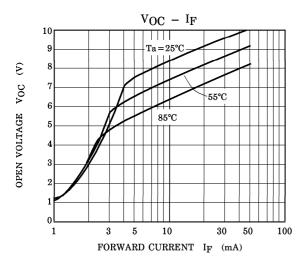
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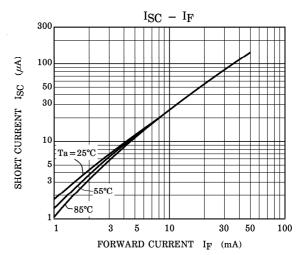












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